

Reet Chaudhuri

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

19
papers

319
citations

9
h-index

17
g-index

21
ext. papers

407
ext. citations

4.4
avg, IF

3.76
L-index

| # | Paper | IF | Citations |
|----|--|-----|-----------|
| 19 | Quantitative scanning microwave microscopy of 2D electron and hole gases in AlN/GaN heterostructures. <i>Applied Physics Letters</i> , 2022 , 120, 012103 | 3.4 | 0 |
| 18 | Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 119, 162104 | 3.4 | 6 |
| 17 | Next generation electronics on the ultrawide-bandgap aluminum nitride platform. <i>Semiconductor Science and Technology</i> , 2021 , 36, 044001 | 1.8 | 17 |
| 16 | High-conductivity polarization-induced 2D hole gases in undoped GaN/AlN heterojunctions enabled by impurity blocking layers. <i>Journal of Applied Physics</i> , 2021 , 130, 025703 | 2.5 | 7 |
| 15 | First RF Power Operation of AlN/GaN/AlN HEMTs With >3 A/mm and 3 W/mm at 10 GHz. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 121-124 | 2.3 | 16 |
| 14 | Electric Fields and Surface Fermi Level in Undoped GaN/AlN Two-Dimensional Hole Gas Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021 , 15, 2000573 | 2.5 | 2 |
| 13 | GaN/AlN p-channel HFETs with $I_{max} > 420$ mA/mm and ~ 20 GHz f_T / f_{MAX} 2020 , | | 6 |
| 12 | Molecular Beam Epitaxy Growth of Large-Area GaN/AlN 2D Hole Gas Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900567 | 1.3 | 9 |
| 11 | Prospects for Wide Bandgap and Ultrawide Bandgap CMOS Devices. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4010-4020 | 2.9 | 38 |
| 10 | A polarization-induced 2D hole gas in undoped gallium nitride quantum wells. <i>Science</i> , 2019 , 365, 1454-1457 | 353 | 57 |
| 9 | Wurtzite phonons and the mobility of a GaN/AlN 2D hole gas. <i>Applied Physics Letters</i> , 2019 , 114, 253501 | 3.4 | 14 |
| 8 | High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1293-1296 | 4.4 | 46 |
| 7 | Molecular beam epitaxial growth of scandium nitride on hexagonal SiC, GaN, and AlN. <i>Applied Physics Letters</i> , 2019 , 115, 172101 | 3.4 | 14 |
| 6 | GaN/AlN Schottky-gate p-channel HFETs with InGaN contacts and 100 mA/mm on-current 2019 , | | 17 |
| 5 | (Invited) GaN-Based Multiple 2DEG Channel BRIDGE (Buried Dual Gate) HEMT Technology for High Power and Linearity. <i>ECS Transactions</i> , 2019 , 92, 103-108 | 1 | 2 |
| 4 | Gate-Recessed E-mode p-Channel HFET With High On-Current Based on GaN/AlN 2D Hole Gas. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1848-1851 | 4.4 | 46 |
| 3 | Terahertz spectroscopy of an electron-hole bilayer system in AlN/GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2017 , 111, 073102 | 3.4 | 8 |

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|---|--|-----|---|
| 2 | Very High Density ($>10^{14}$ cm $^{-2}$) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. <i>Advanced Electronic Materials</i> ,2101120 | 6.4 | 3 |
| 1 | In Situ Crystalline AlN Passivation for Reduced RF Dispersion in Strained-Channel AlN/GaN/AlN High-Electron-Mobility Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> ,2100452 | 1.6 | 5 |